

Claims

What is claimed:

1. A semiconductor device, comprising:
a semiconductor die including a notch formed in a peripheral region of an active surface of the semiconductor die;
an encapsulant deposited around the semiconductor die and into the notch, wherein a surface of the encapsulant is coplanar with the notched active surface of the semiconductor die; and
a build-up interconnect structure formed over the semiconductor die and entirely within a footprint of the semiconductor die.
2. The semiconductor device of claim 1, wherein the build-up interconnect structure further includes:
an insulating layer formed over the semiconductor die; and
a conductive layer formed over the insulating layer, the encapsulant devoid of the conductive layer.
3. The semiconductor device of claim 1, wherein a non-active surface of the semiconductor die is exposed with respect to the encapsulant.
4. The semiconductor device of claim 1, wherein the encapsulant covers a sidewall of the semiconductor die.
5. The semiconductor device of claim 4, wherein the encapsulant covering the sidewall of the semiconductor die includes a thickness of 50 micrometers (μm) or less.